

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claim 1 (currently amended) A manufacturing method of a semiconductor device, comprising the steps of:

- a step of forming a plurality of electrodes on a front face of a semiconductor chip;
- a step of covering the front face of the semiconductor chip with a resin insulating film;
- a step of covering all of an upper surface and side surfaces of said resin insulating film with a metal protective film so that said metal protective film contacts said resin insulating film and extends to a surface of said semiconductor chip; and
- a step of providing an electrical connecting portion of at least any of the plurality of electrodes at a reverse face of the semiconductor chip.

Claim 2 (previously presented) The manufacturing method of the semiconductor device according to claim 1,

wherein a metal layer forming a portion of said metal protective film<sub>is</sub> formed on a peripheral isolation region on the front face of the semiconductor chip when covering the side surface of the resin insulating film with the metal protective film.

Claim 3 (original) The manufacturing method of the semiconductor device according to claim 1, further comprising the step of:

a step of exposing one of the plurality of electrodes from the upper surface of said resin insulating film to be connected to the metal protective film.

Claim 4 (previously presented) The manufacturing method of the semiconductor device according to claim 1,

wherein the metal protective film comprises an upper surface protecting film covering an upper surface of the resin insulating film and a side surface protecting film covering a side surface of the resin insulating film.